

AMENDMENTS TO THE SPECIFICATION

Please replace the first full paragraph on page 4 with the following amended paragraph:

Referring to FIG. 1C, subsequently, a second etch stop layer 128, e.g., a nitride layer is formed on top faces of the second contact plug 126 and the third insulating layer 122 to prevent a damage of the second plug 126 during a post etching step for forming a capacitor bottom electrode 134. Next, a sacrificial layer 130 is formed on the top face of the second etch stop layer 128 with a predetermined thickness in consideration of the height of the designed capacitor. Then, a second photoresist layer is formed on the sacrificial layer 130 and is patterned into a fourth predetermined configuration so that a second photoresist pattern ~~132~~ 136 is formed.

Please replace the second full paragraph on page 4 with the following amended paragraph:

Thereafter, the sacrificial layer 130 is patterned using the second photoresist pattern ~~132~~ 136 as an etching mask. A first etching step is carried out till the top face of the second etch stop layer 128 is exposed and a second etching step is carried out till the top face of the second plug 126 is exposed, thereby obtaining an opening 131. Here, polysilicon may

be used as a hard mask between the sacrificial layer 130 and the second photoresist pattern ~~132~~ 136. Then, the second photoresist pattern ~~132~~ 136 is removed as shown in FIG. 1D.

Please replace the paragraph bridging pages 4 and 5 with the following amended paragraph:

In a next step as shown in FIG. 1E, a conductive layer 132 is deposited over the resultant structure including the opening ~~132~~ 131 with uniform thickness so that the conductive layer 132 is electrically connected to the second contact plug 126. After forming the conductive layer 132, a photoresist is deposited to fill a concave part of the conductive layer 132 completely.